



30V N-Channel Enhancement Mode MOSFET - ESD Protected

Voltage

30 V

Current

350mA

Features

- RDS(ON), VGS@4.5V, ID@350mA<1.2Ω
- RDS(ON), VGS@2.5V, ID@200mA<1.6Ω
- RDS(ON), VGS@1.8V, ID@80mA<2.3Ω
- RDS(ON), VGS@1.5V, ID@10mA<2.5Ω(typ.)
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

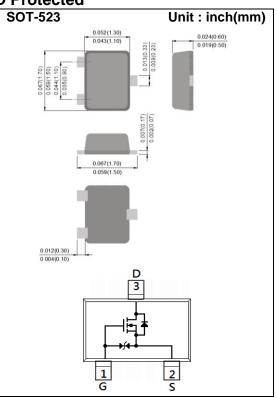
Mechanical Data

• Case: SOT-523 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.002 grams

• Marking: E12



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	30	V
Gate-Source Voltage		V _{GS}	<u>+</u> 10	V
Continuous Drain Current		ID	350	mA
Pulsed Drain Current		I _{DM}	1400	mA
Power Dissipation	T _a =25°C	P _D	300	mW
	Derate above 25°C		2.4	mW/°C
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C
Typical Thermal Resistance - Junction to Ambient ^(Note 3)		$R_{ hetaJA}$	417	°C/W
- Sunction to Ambient(************************************		5074		-0/00





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	30	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	0.6	0.85	1.1	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =350mA	-	0.94	1.2	Ω
		V _{GS} =2.5V, I _D =200mA	-	1.32	1.6	
		V _{GS} =1.8V, I _D =80mA	-	1.82	2.3	
		V _{GS} =1.5V, I _D =10mA	-	2.5	-	
Zero Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0V	-	0.01	1	
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 8V, V _{DS} =0V	-	-	<u>+</u> 10	uA
		V _{GS} = <u>+</u> 5V, V _{DS} =0V	-	-	<u>+</u> 1	
Dynamic ^(Note 5)						
Total Gate Charge	Q_g	V _{DS} =15V, I _D =350mA, V _{GS} =4.5V ^(Note 1,2)	-	0.87	-	nC
Gate-Source Charge	Q_gs		-	0.26	-	
Gate-Drain Charge	Q_gd		-	0.16	-	
Input Capacitance	Ciss	\/ 45\/ \/ O\/	-	34	-	pF
Output Capacitance	Coss	V _{DS} =15V, V _{GS} =0V,	-	8.9	-	
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	2.5	-	
Turn-On Delay Time	td _(on)	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	-	7.1	-	ns
Turn-On Rise Time	tr	V_{DD} =15V, I_{D} =80mA, V_{GS} =4.0V, R_{G} =6 Ω (Note 1,2)	-	20	-	
Turn-Off Delay Time	td _(off)		-	41	-	
Turn-Off Fall Time	tf	KG=012(1010 1,2)	-	31	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	Is		-	-	350	mA
Diode Forward Voltage	V _{SD}	I _S =350mA, V _{GS} =0V	_	0.88	1.3	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
- 4. The maximum current rating is package limited
- 5. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

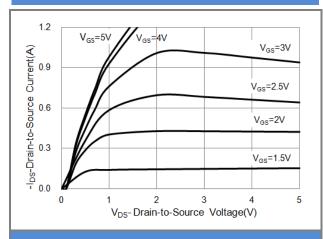


Fig.1 On-Region Characteristics

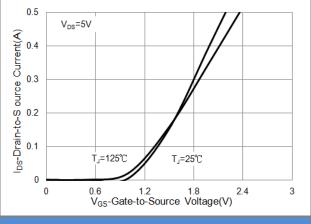


Fig.2 Transfer Characteristics

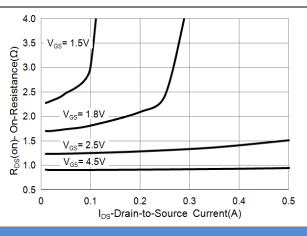


Fig.3 On-Resistance vs. Drain Current

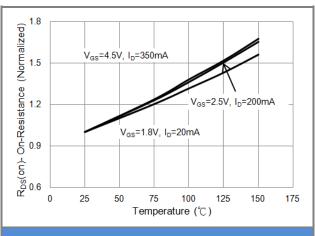


Fig.4 On-Resistance vs. Junction temperature

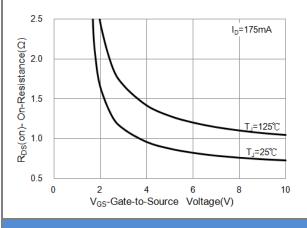


Fig.5 On-Resistance Variation with VGS.

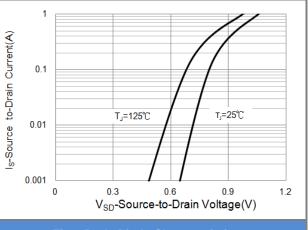


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

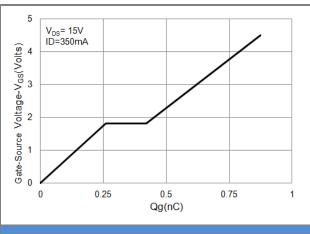


Fig.7 Gate-Charge Characteristics

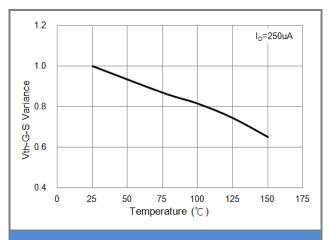


Fig.8 Threshold Voltage Variation with Temperature.

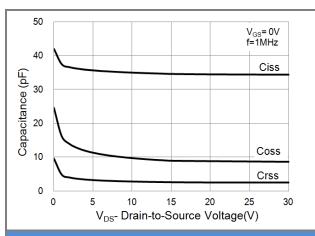


Fig.9 Capacitance vs. Drain-Source Voltage.

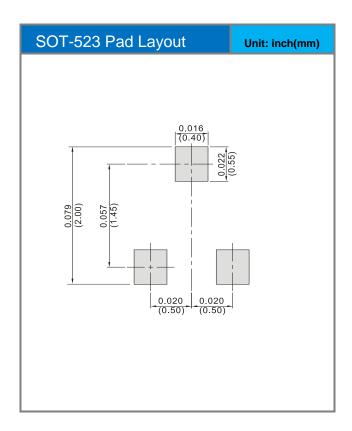




PART NO. PACKING CODE VERSION

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJE8412_R1_00001	SOT-523	4K pcs / 7" reel	E12	Halogen free RoHS compliant

MOUNTING PAD LAYOUT







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